

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-GSM850-251CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 89.59 V/m; Power Drift = 0.00 dB

PMF = 2.830 is applied.

E-field emissions = 194.1 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

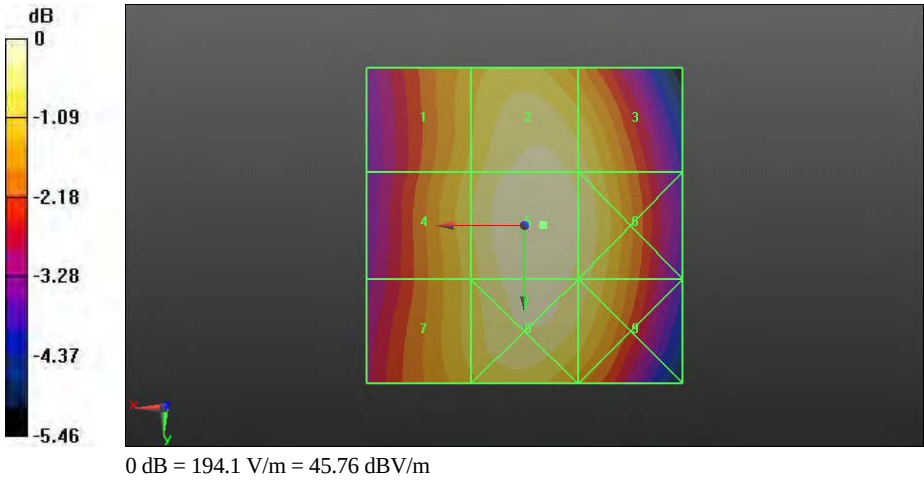
Grid 1 M3 174.0 V/m	Grid 2 M3 189.7 V/m	Grid 3 M3 182.8 V/m
Grid 4 M3 177.8 V/m	Grid 5 M3 194.1 V/m	Grid 6 M3 187.3 V/m
Grid 7 M3 175.1 V/m	Grid 8 M3 190.1 V/m	Grid 9 M3 183.5 V/m

Cursor:

Total = 194.1 V/m

E Category: M3

Location: -3, 0, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-GSM850-190CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 98.74 V/m; Power Drift = 0.02 dB

PMF = 2.830 is applied.

E-field emissions = 212.7 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

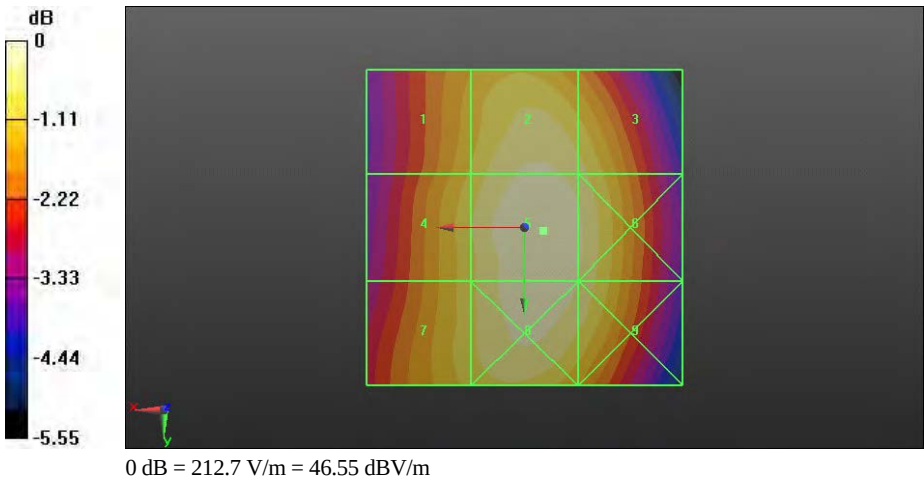
Grid 1 M3 188.6 V/m	Grid 2 M3 205.9 V/m	Grid 3 M3 199.2 V/m
Grid 4 M3 194.7 V/m	Grid 5 M3 212.7 V/m	Grid 6 M3 205.4 V/m
Grid 7 M3 193.4 V/m	Grid 8 M3 210.3 V/m	Grid 9 M3 203.5 V/m

Cursor:

Total = 212.7 V/m

E Category: M3

Location: -3, 0.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-GSM850-128CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 110.0 V/m; Power Drift = -0.03 dB

PMF = 2.830 is applied.

E-field emissions = 236.6 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

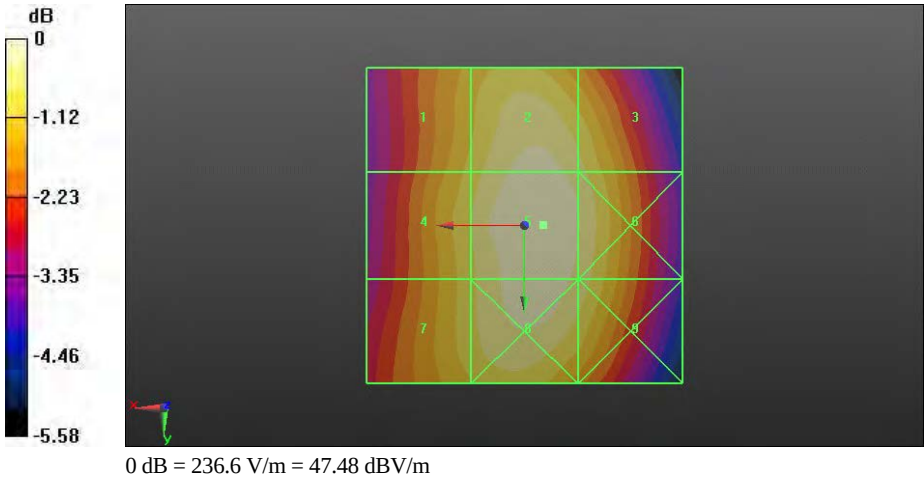
Grid 1 M3 211.7 V/m	Grid 2 M3 231.0 V/m	Grid 3 M3 221.1 V/m
Grid 4 M3 217.4 V/m	Grid 5 M3 236.6 V/m	Grid 6 M3 227.5 V/m
Grid 7 M3 214.7 V/m	Grid 8 M3 232.2 V/m	Grid 9 M3 223.5 V/m

Cursor:

Total = 236.6 V/m

E Category: M3

Location: -3, 0, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-GSM850-128CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 110.6 V/m; Power Drift = 0.01 dB

PMF = 2.830 is applied.

E-field emissions = 238.0 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

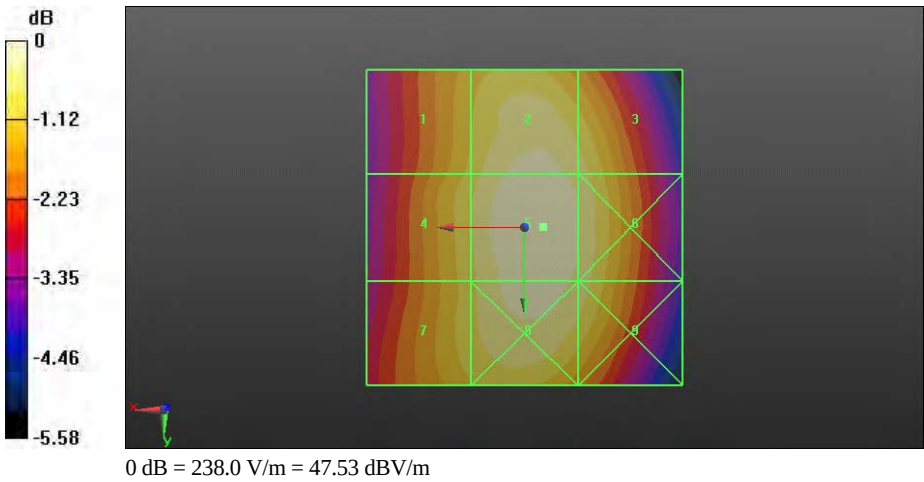
Grid 1 M3	Grid 2 M3	Grid 3 M3
212.9 V/m	232.2 V/m	223.8 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
218.3 V/m	238.0 V/m	228.2 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
215.9 V/m	233.8 V/m	225.0 V/m

Cursor:

Total = 238.0 V/m

E Category: M3

Location: -3, 0, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-GSM850-251CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07100 A/m; Power Drift = 0.10 dB

PMF = 2.820 is applied.

H-field emissions = 0.2716 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

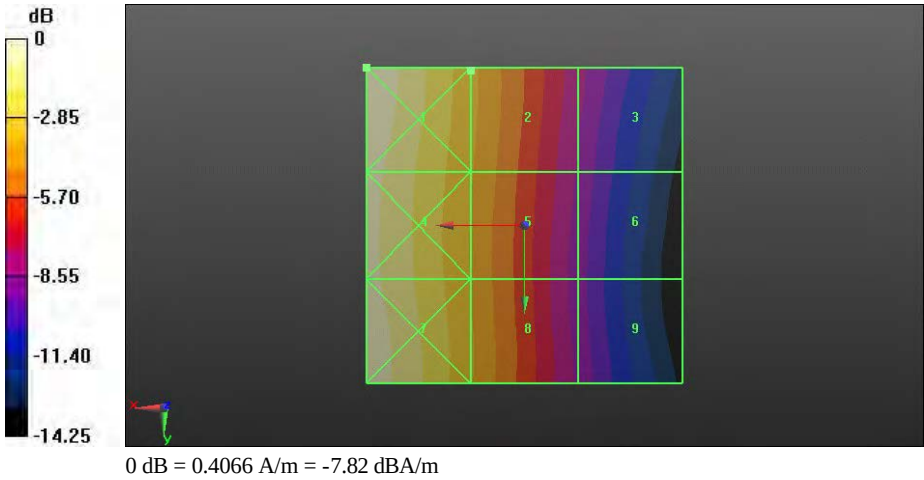
Grid 1 M4 0.407 A/m	Grid 2 M4 0.272 A/m	Grid 3 M4 0.158 A/m
Grid 4 M4 0.385 A/m	Grid 5 M4 0.266 A/m	Grid 6 M4 0.150 A/m
Grid 7 M4 0.397 A/m	Grid 8 M4 0.267 A/m	Grid 9 M4 0.149 A/m

Cursor:

Total = 0.4066 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-GSM850-190CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07800 A/m; Power Drift = -0.04 dB

PMF = 2.820 is applied.

H-field emissions = 0.3034 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

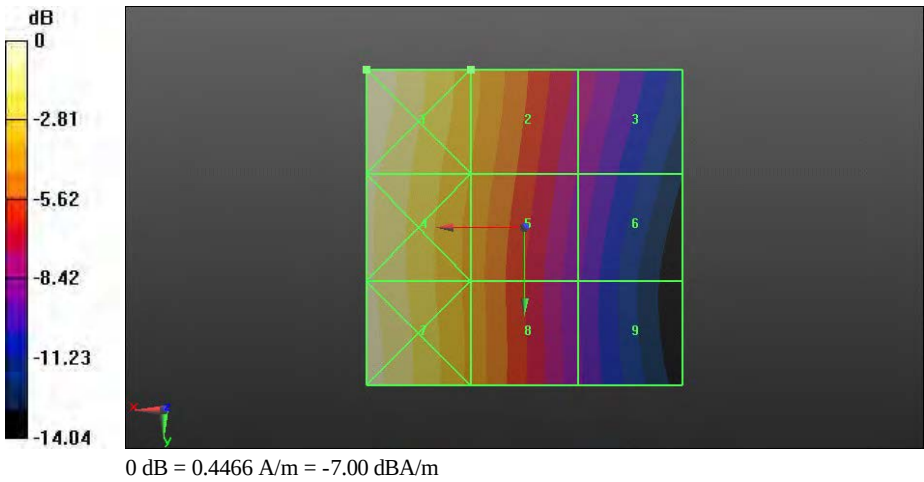
Grid 1 M4 0.447 A/m	Grid 2 M4 0.303 A/m	Grid 3 M4 0.185 A/m
Grid 4 M4 0.416 A/m	Grid 5 M4 0.289 A/m	Grid 6 M4 0.169 A/m
Grid 7 M4 0.424 A/m	Grid 8 M4 0.283 A/m	Grid 9 M4 0.156 A/m

Cursor:

Total = 0.4466 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-GSM850-128CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08300 A/m; Power Drift = 0.02 dB

PMF = 2.820 is applied.

H-field emissions = 0.3124 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

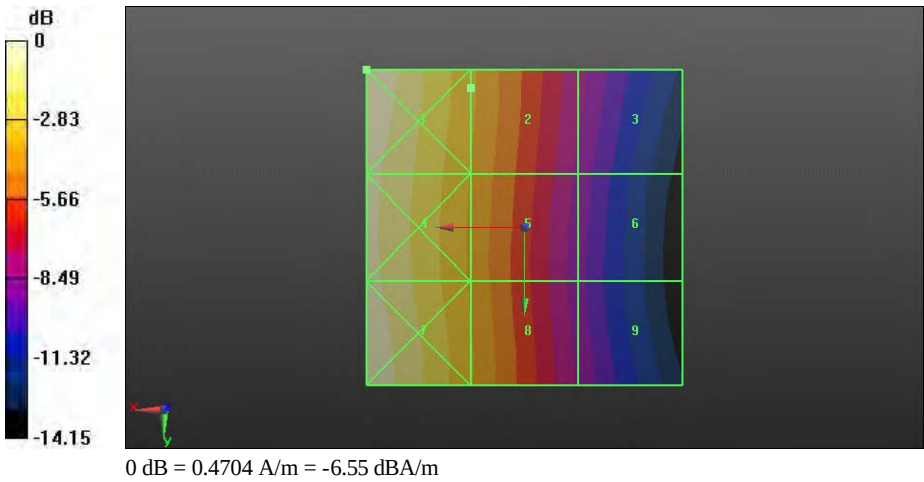
Grid 1 M3 0.470 A/m	Grid 2 M4 0.312 A/m	Grid 3 M4 0.184 A/m
Grid 4 M4 0.443 A/m	Grid 5 M4 0.304 A/m	Grid 6 M4 0.173 A/m
Grid 7 M3 0.462 A/m	Grid 8 M4 0.310 A/m	Grid 9 M4 0.175 A/m

Cursor:

Total = 0.4704 A/m

H Category: M3

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-GSM850-128CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08400 A/m; Power Drift = -0.02 dB

PMF = 2.820 is applied.

H-field emissions = 0.3170 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

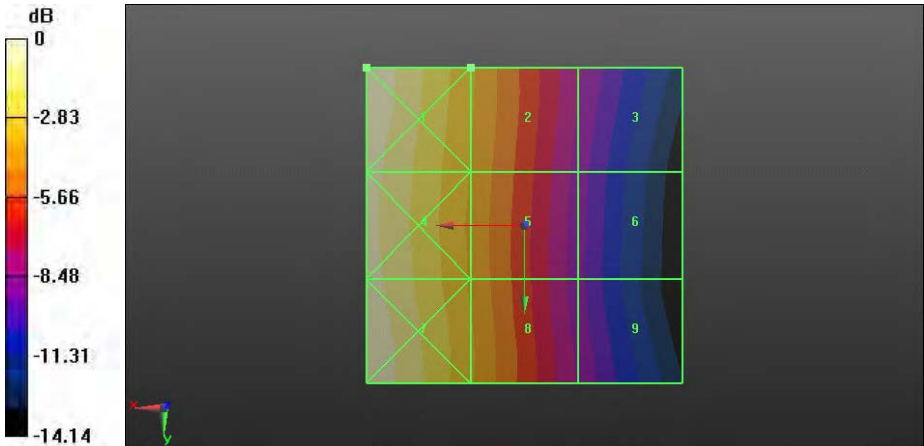
Grid 1 M3 0.479 A/m	Grid 2 M4 0.317 A/m	Grid 3 M4 0.185 A/m
Grid 4 M3 0.453 A/m	Grid 5 M4 0.309 A/m	Grid 6 M4 0.173 A/m
Grid 7 M3 0.473 A/m	Grid 8 M4 0.317 A/m	Grid 9 M4 0.179 A/m

Cursor:

Total = 0.4794 A/m

H Category: M3

Location: 25, -25, 8.7 mm



0 dB = 0.4794 A/m = -6.39 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-GSM1900-810CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 22.35 V/m; Power Drift = -0.02 dB

PMF = 2.860 is applied.

E-field emissions = 59.28 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

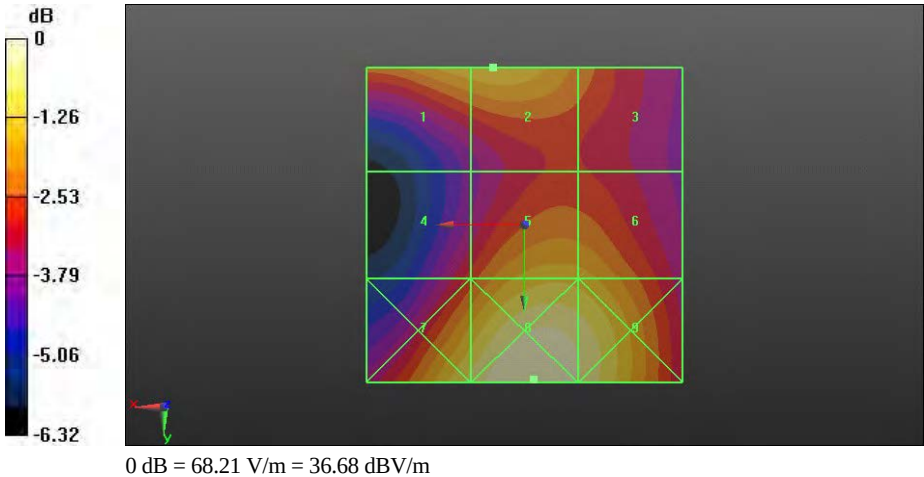
Grid 1 M3 58.70 V/m	Grid 2 M3 59.28 V/m	Grid 3 M3 52.90 V/m
Grid 4 M3 49.87 V/m	Grid 5 M3 58.49 V/m	Grid 6 M3 57.80 V/m
Grid 7 M3 63.12 V/m	Grid 8 M3 68.21 V/m	Grid 9 M3 65.27 V/m

Cursor:

Total = 68.21 V/m

E Category: M3

Location: -1.5, 24.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-GSM1900-661CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 19.57 V/m; Power Drift = -0.02 dB

PMF = 2.860 is applied.

E-field emissions = 62.35 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

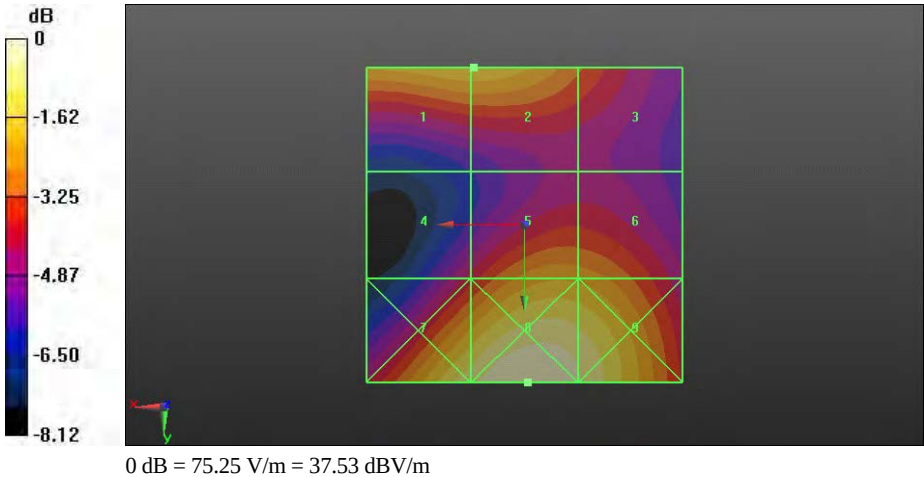
Grid 1 M3	Grid 2 M3	Grid 3 M3
62.33 V/m	62.35 V/m	52.58 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
47.35 V/m	58.37 V/m	57.81 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
69.63 V/m	75.25 V/m	71.30 V/m

Cursor:

Total = 75.25 V/m

E Category: M3

Location: -0.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-GSM1900-512CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 16.56 V/m; Power Drift = 0.00 dB

PMF = 2.860 is applied.

E-field emissions = 60.31 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

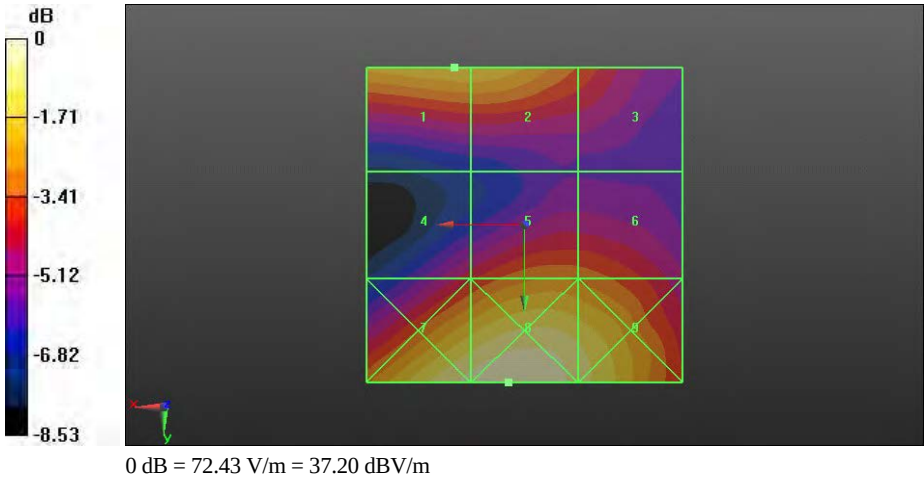
Grid 1 M3 60.31 V/m	Grid 2 M3 60.16 V/m	Grid 3 M3 48.74 V/m
Grid 4 M4 45.15 V/m	Grid 5 M3 52.59 V/m	Grid 6 M3 51.49 V/m
Grid 7 M3 69.99 V/m	Grid 8 M3 72.43 V/m	Grid 9 M3 65.86 V/m

Cursor:

Total = 72.43 V/m

E Category: M3

Location: 2.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-GSM1900-661CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 19.96 V/m; Power Drift = -0.03 dB

PMF = 2.860 is applied.

E-field emissions = 62.71 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

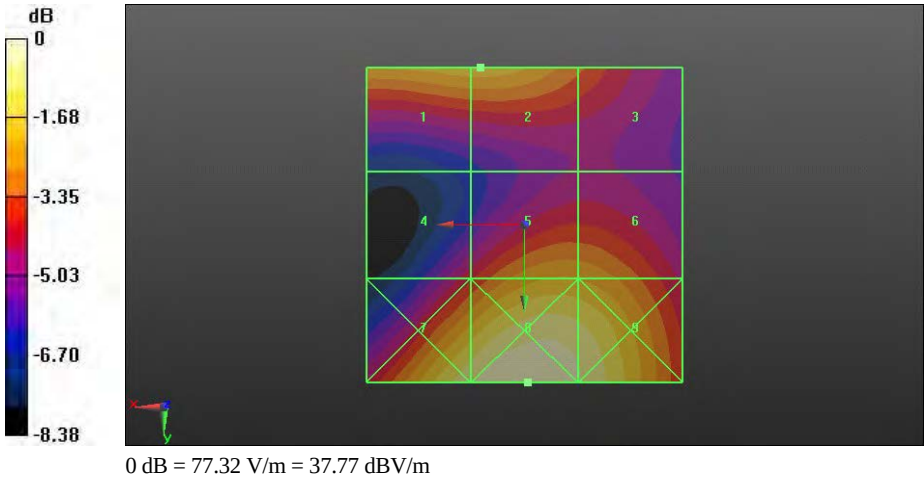
Grid 1 M3	Grid 2 M3	Grid 3 M3
62.60 V/m	62.71 V/m	53.67 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
48.81 V/m	60.24 V/m	59.74 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
71.86 V/m	77.32 V/m	72.93 V/m

Cursor:

Total = 77.32 V/m

E Category: M3

Location: -0.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-GSM1900-810CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06700 A/m; Power Drift = -0.07 dB

PMF = 2.830 is applied.

H-field emissions = 0.1811 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

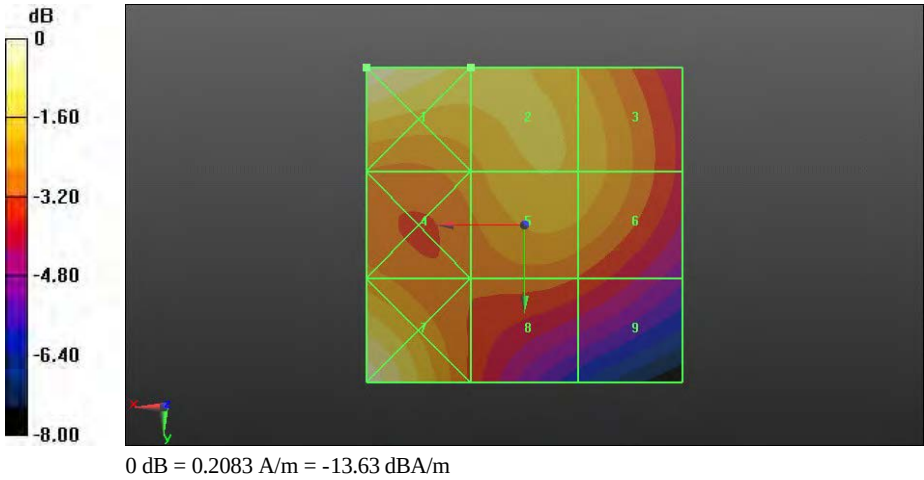
Grid 1 M3 0.208 A/m	Grid 2 M3 0.181 A/m	Grid 3 M3 0.171 A/m
Grid 4 M3 0.159 A/m	Grid 5 M3 0.174 A/m	Grid 6 M3 0.171 A/m
Grid 7 M3 0.204 A/m	Grid 8 M3 0.149 A/m	Grid 9 M3 0.143 A/m

Cursor:

Total = 0.2083 A/m

H Category: M3

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-GSM1900-661CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07800 A/m; Power Drift = -0.01 dB

PMF = 2.830 is applied.

H-field emissions = 0.1975 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

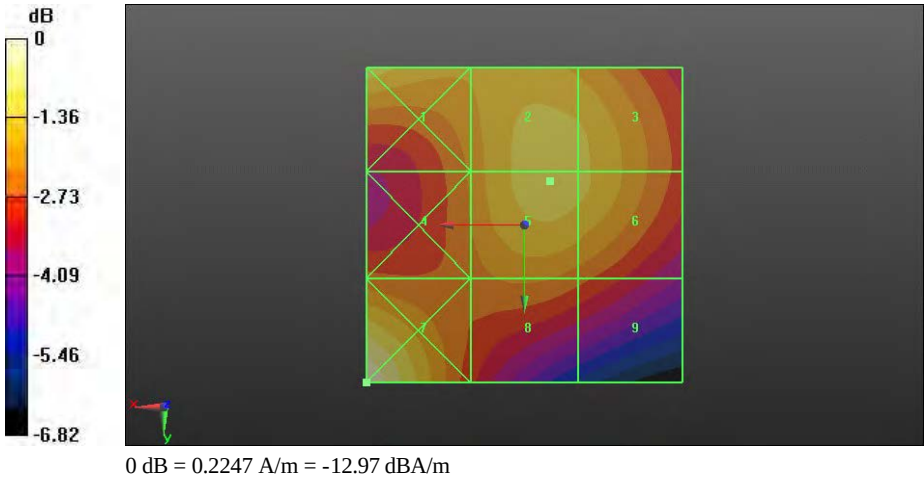
Grid 1 M3 0.201 A/m	Grid 2 M3 0.197 A/m	Grid 3 M3 0.195 A/m
Grid 4 M3 0.175 A/m	Grid 5 M3 0.198 A/m	Grid 6 M3 0.195 A/m
Grid 7 M3 0.225 A/m	Grid 8 M3 0.175 A/m	Grid 9 M3 0.168 A/m

Cursor:

Total = 0.2247 A/m

H Category: M3

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-GSM1900-512CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07400 A/m; Power Drift = -0.02 dB

PMF = 2.830 is applied.

H-field emissions = 0.1894 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

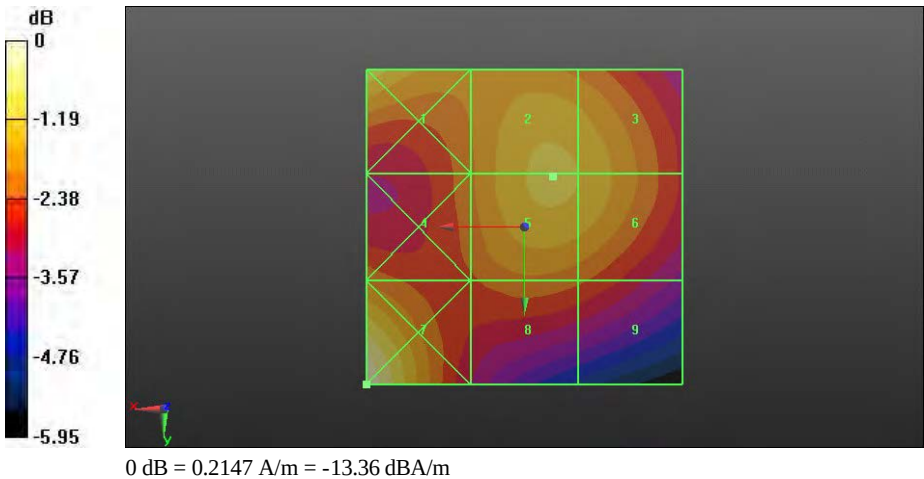
Grid 1 M3 0.197 A/m	Grid 2 M3 0.189 A/m	Grid 3 M3 0.187 A/m
Grid 4 M3 0.170 A/m	Grid 5 M3 0.189 A/m	Grid 6 M3 0.187 A/m
Grid 7 M3 0.215 A/m	Grid 8 M3 0.169 A/m	Grid 9 M3 0.165 A/m

Cursor:

Total = 0.2147 A/m

H Category: M3

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-GSM1900-661CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07700 A/m; Power Drift = -0.02 dB

PMF = 2.830 is applied.

H-field emissions = 0.1932 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

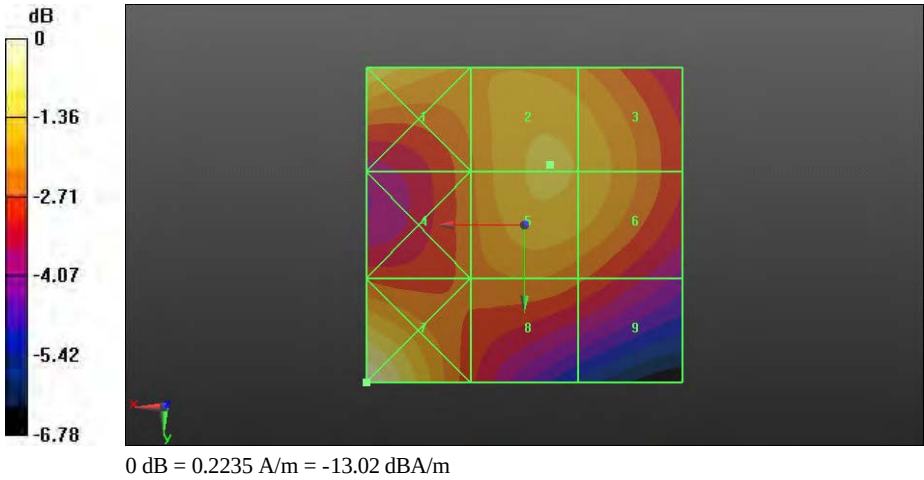
Grid 1 M3 0.204 A/m	Grid 2 M3 0.193 A/m	Grid 3 M3 0.191 A/m
Grid 4 M3 0.170 A/m	Grid 5 M3 0.193 A/m	Grid 6 M3 0.191 A/m
Grid 7 M3 0.223 A/m	Grid 8 M3 0.173 A/m	Grid 9 M3 0.166 A/m

Cursor:

Total = 0.2235 A/m

H Category: M3

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band II-9538CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 26.93 V/m; Power Drift = 0.02 dB

PMF = 1.020 is applied.

E-field emissions = 26.36 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

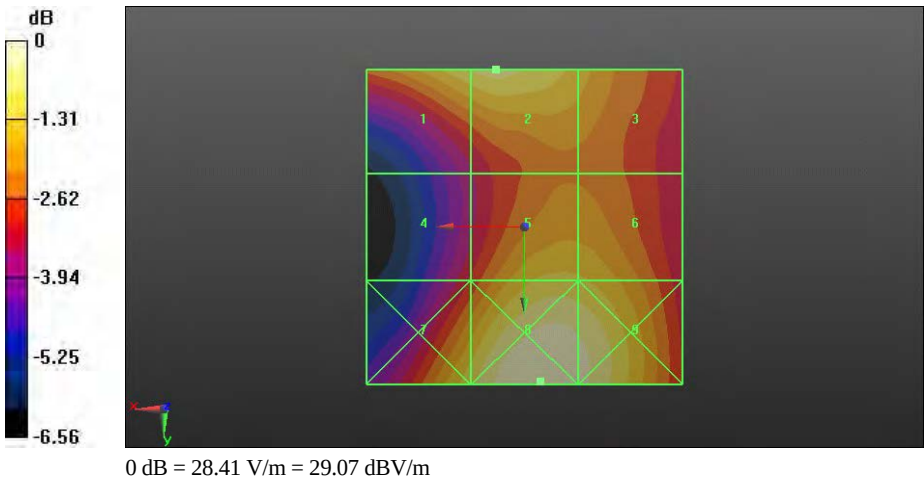
Grid 1 M4	Grid 2 M4	Grid 3 M4
25.77 V/m	26.36 V/m	23.86 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
20.22 V/m	24.94 V/m	24.71 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
25.46 V/m	28.41 V/m	27.57 V/m

Cursor:

Total = 28.41 V/m

E Category: M4

Location: -2.5, 24.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band II-9400CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 24.91 V/m; Power Drift = 0.01 dB

PMF = 1.020 is applied.

E-field emissions = 28.44 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

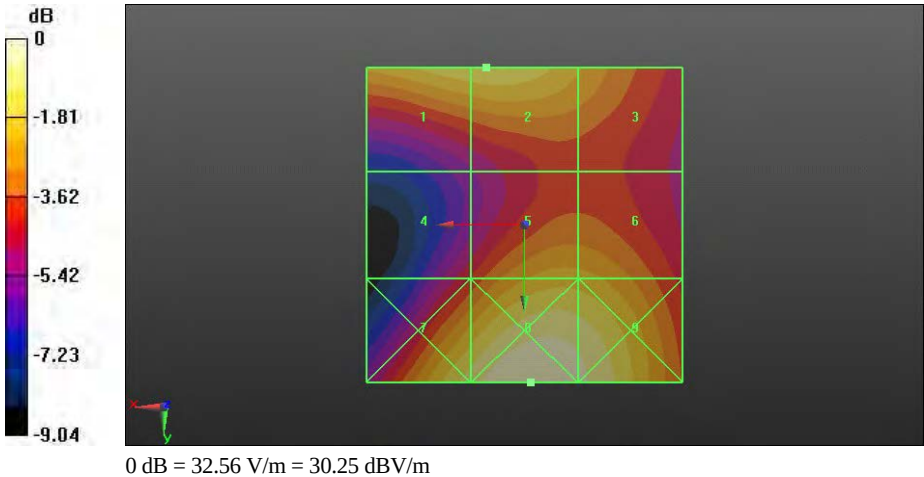
Grid 1 M4	Grid 2 M4	Grid 3 M4
28.27 V/m	28.44 V/m	24.98 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
20.30 V/m	25.70 V/m	25.52 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
29.50 V/m	32.56 V/m	31.00 V/m

Cursor:

Total = 32.56 V/m

E Category: M4

Location: -1, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band II-9262CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 22.81 V/m; Power Drift = 0.02 dB

PMF = 1.020 is applied.

E-field emissions = 30.11 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

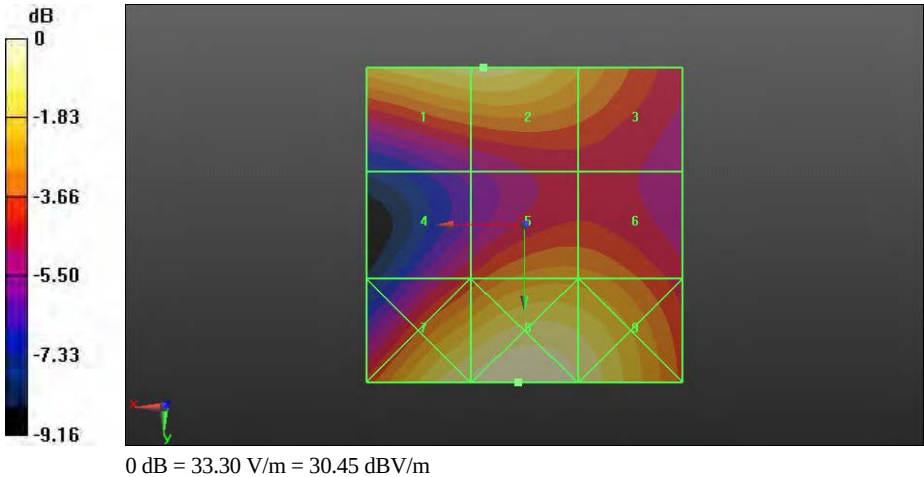
Grid 1 M4 30.01 V/m	Grid 2 M4 30.11 V/m	Grid 3 M4 25.46 V/m
Grid 4 M4 20.83 V/m	Grid 5 M4 24.67 V/m	Grid 6 M4 24.47 V/m
Grid 7 M4 31.58 V/m	Grid 8 M4 33.30 V/m	Grid 9 M4 30.90 V/m

Cursor:

Total = 33.30 V/m

E Category: M4

Location: 1, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band II-9262CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 22.88 V/m; Power Drift = 0.06 dB

PMF = 1.020 is applied.

E-field emissions = 27.05 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

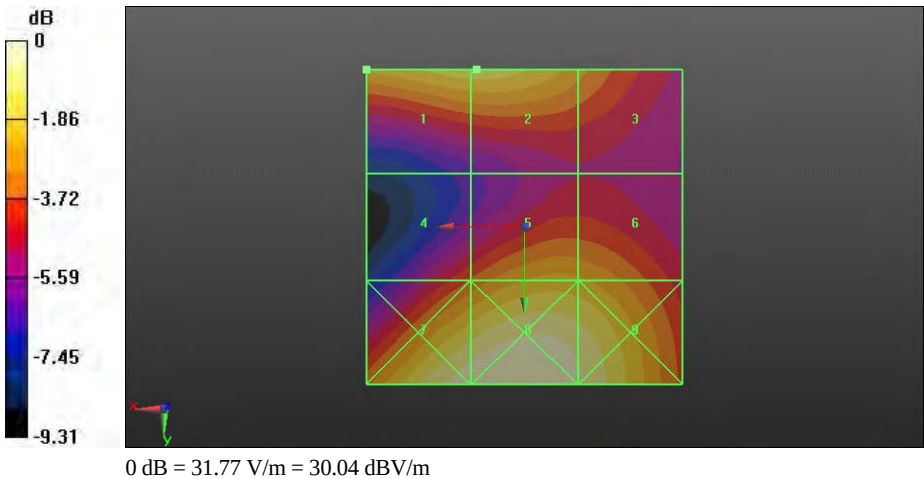
Grid 1 M4	Grid 2 M4	Grid 3 M4
27.01 V/m	27.05 V/m	22.95 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
20.93 V/m	24.60 V/m	24.24 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
31.39 V/m	32.41 V/m	29.86 V/m

Cursor:

Total = 24.31 V/m

E Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band II-9538CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07300 A/m; Power Drift = 0.01 dB

PMF = 1.010 is applied.

H-field emissions = 0.07555 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

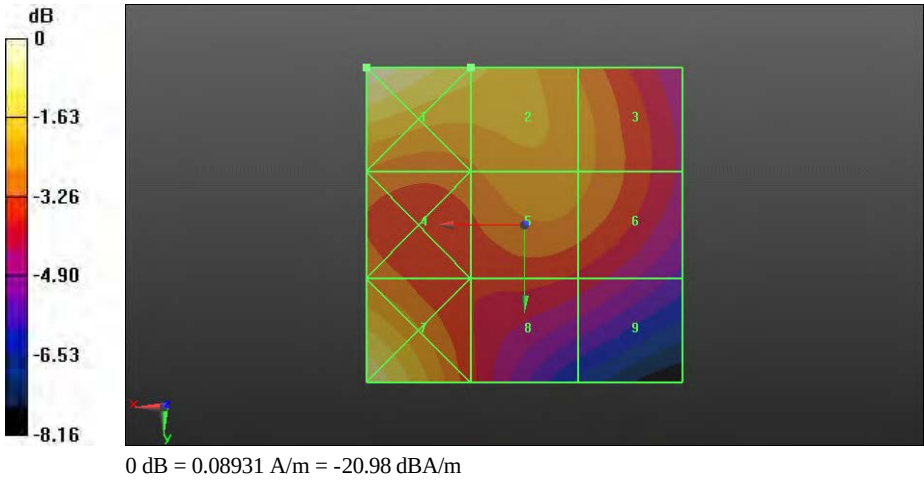
Grid 1 M4 0.089 A/m	Grid 2 M4 0.076 A/m	Grid 3 M4 0.067 A/m
Grid 4 M4 0.065 A/m	Grid 5 M4 0.069 A/m	Grid 6 M4 0.067 A/m
Grid 7 M4 0.084 A/m	Grid 8 M4 0.059 A/m	Grid 9 M4 0.057 A/m

Cursor:

Total = 0.08931 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band II-9400CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08700 A/m; Power Drift = 0.03 dB

PMF = 1.010 is applied.

H-field emissions = 0.08007 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

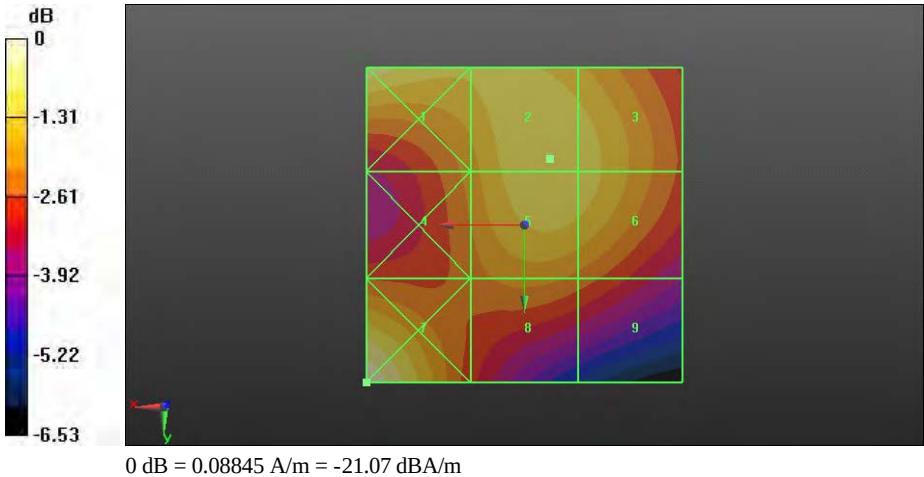
Grid 1 M4 0.083 A/m	Grid 2 M4 0.080 A/m	Grid 3 M4 0.079 A/m
Grid 4 M4 0.071 A/m	Grid 5 M4 0.080 A/m	Grid 6 M4 0.079 A/m
Grid 7 M4 0.088 A/m	Grid 8 M4 0.070 A/m	Grid 9 M4 0.068 A/m

Cursor:

Total = 0.08845 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band II-9262CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08700 A/m; Power Drift = 0.03 dB

PMF = 1.010 is applied.

H-field emissions = 0.07910 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

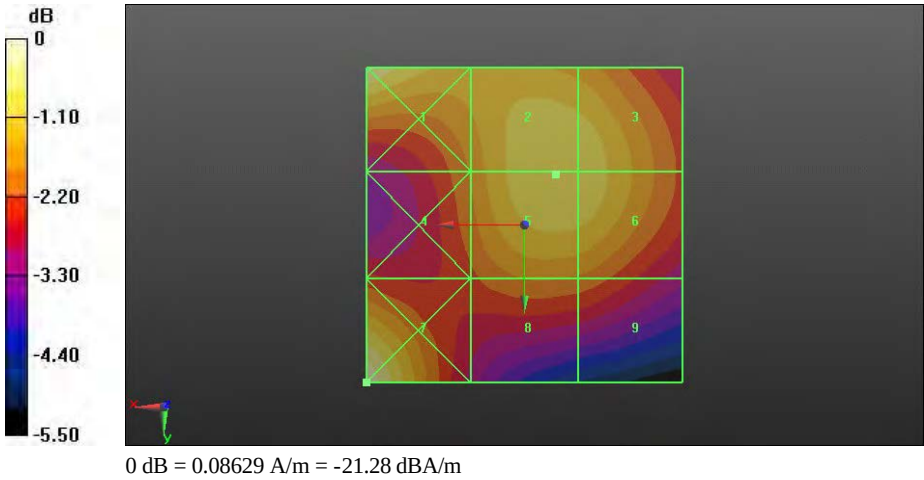
Grid 1 M4 0.085 A/m	Grid 2 M4 0.079 A/m	Grid 3 M4 0.079 A/m
Grid 4 M4 0.070 A/m	Grid 5 M4 0.079 A/m	Grid 6 M4 0.079 A/m
Grid 7 M4 0.086 A/m	Grid 8 M4 0.070 A/m	Grid 9 M4 0.069 A/m

Cursor:

Total = 0.08629 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band II-9400CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08700 A/m; Power Drift = -0.03 dB

PMF = 1.010 is applied.

H-field emissions = 0.07870 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

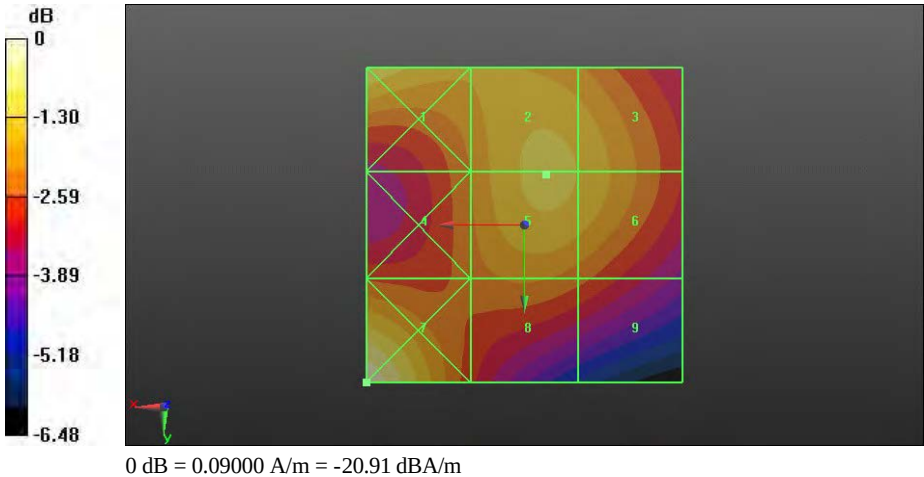
Grid 1 M4 0.083 A/m	Grid 2 M4 0.079 A/m	Grid 3 M4 0.077 A/m
Grid 4 M4 0.070 A/m	Grid 5 M4 0.079 A/m	Grid 6 M4 0.077 A/m
Grid 7 M4 0.090 A/m	Grid 8 M4 0.071 A/m	Grid 9 M4 0.068 A/m

Cursor:

Total = 0.09000 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band IV-1513CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 29.26 V/m; Power Drift = -0.02 dB

PMF = 1.020 is applied.

E-field emissions = 33.18 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

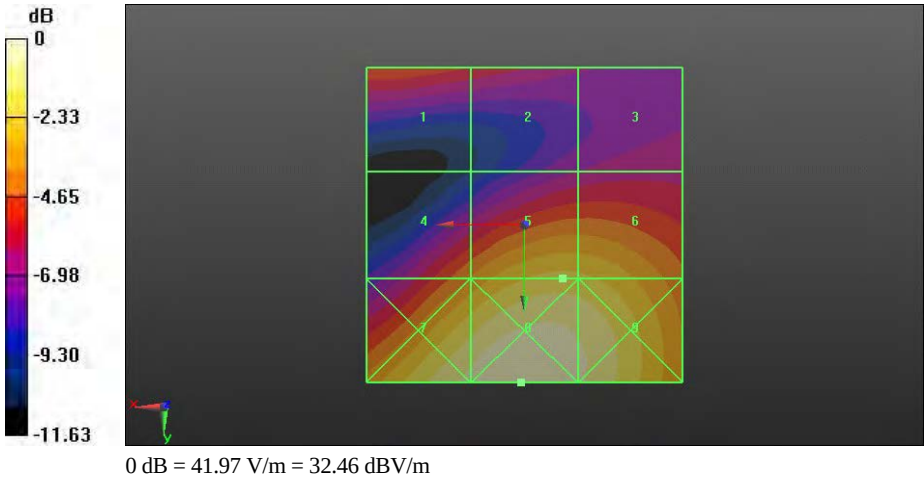
Grid 1 M4	Grid 2 M4	Grid 3 M4
24.75 V/m	22.60 V/m	20.05 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
27.17 V/m	33.18 V/m	32.91 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
39.61 V/m	41.97 V/m	39.18 V/m

Cursor:

Total = 41.97 V/m

E Category: M4

Location: 0.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band IV-1413CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 32.89 V/m; Power Drift = -0.02 dB

PMF = 1.020 is applied.

E-field emissions = 36.68 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

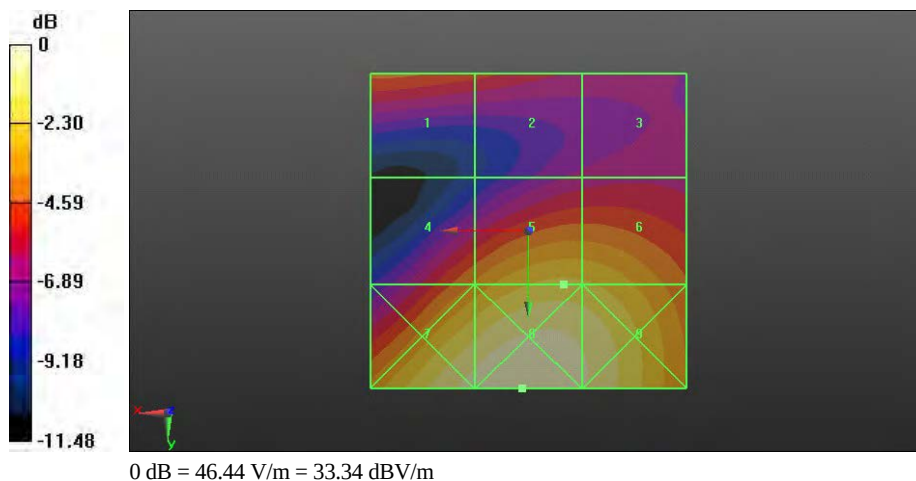
Grid 1 M4 28.38 V/m	Grid 2 M4 26.26 V/m	Grid 3 M4 22.62 V/m
Grid 4 M4 30.54 V/m	Grid 5 M4 36.68 V/m	Grid 6 M4 36.33 V/m
Grid 7 M4 44.33 V/m	Grid 8 M4 46.44 V/m	Grid 9 M4 43.10 V/m

Cursor:

Total = 46.44 V/m

E Category: M4

Location: 1, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band IV-1312CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 32.23 V/m; Power Drift = -0.01 dB

PMF = 1.020 is applied.

E-field emissions = 36.26 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

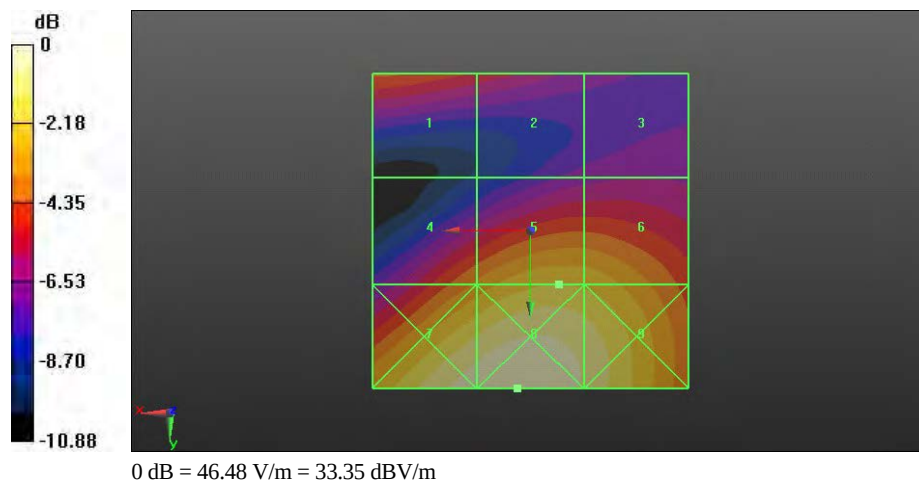
Grid 1 M4 28.85 V/m	Grid 2 M4 25.76 V/m	Grid 3 M4 21.93 V/m
Grid 4 M4 31.35 V/m	Grid 5 M4 36.26 V/m	Grid 6 M4 35.72 V/m
Grid 7 M4 45.08 V/m	Grid 8 M4 46.48 V/m	Grid 9 M4 42.34 V/m

Cursor:

Total = 46.48 V/m

E Category: M4

Location: 2, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band IV-1413CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 31.62 V/m; Power Drift = -0.01 dB

PMF = 1.020 is applied.

E-field emissions = 36.24 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

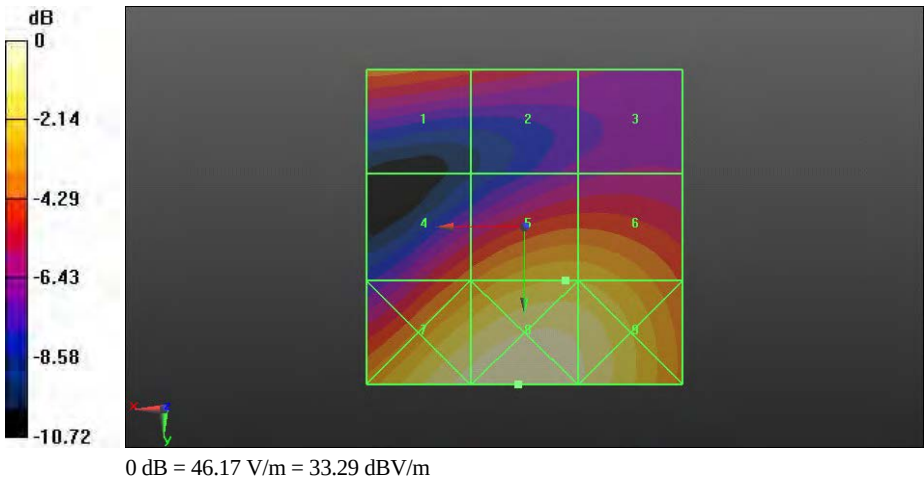
Grid 1 M4	Grid 2 M4	Grid 3 M4
29.61 V/m	26.82 V/m	22.81 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
30.15 V/m	36.24 V/m	36.08 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
44.32 V/m	46.17 V/m	43.21 V/m

Cursor:

Total = 46.17 V/m

E Category: M4

Location: 1, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band IV-1513CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1090 A/m; Power Drift = -0.03 dB

PMF = 0.9800 is applied.

H-field emissions = 0.09572 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

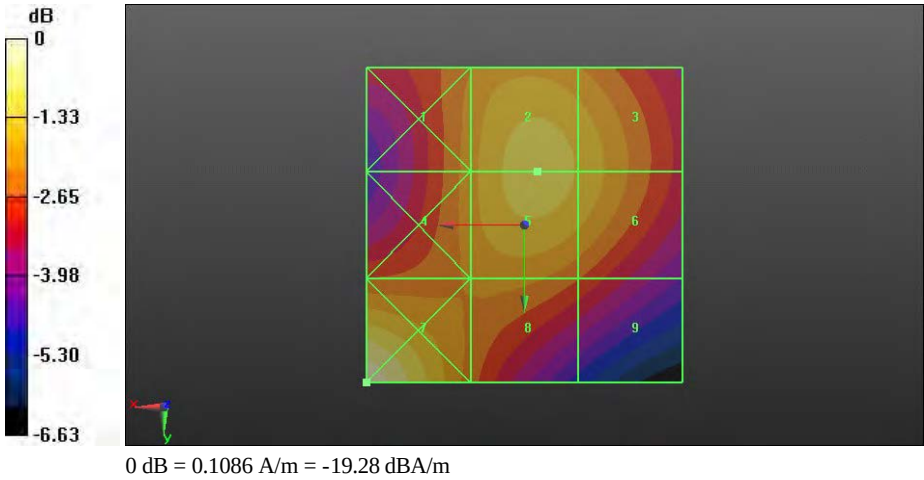
Grid 1 M4 0.087 A/m	Grid 2 M4 0.096 A/m	Grid 3 M4 0.093 A/m
Grid 4 M4 0.087 A/m	Grid 5 M4 0.096 A/m	Grid 6 M4 0.093 A/m
Grid 7 M4 0.109 A/m	Grid 8 M4 0.086 A/m	Grid 9 M4 0.080 A/m

Cursor:

Total = 0.1086 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band IV-1413CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1270 A/m; Power Drift = -0.03 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1103 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

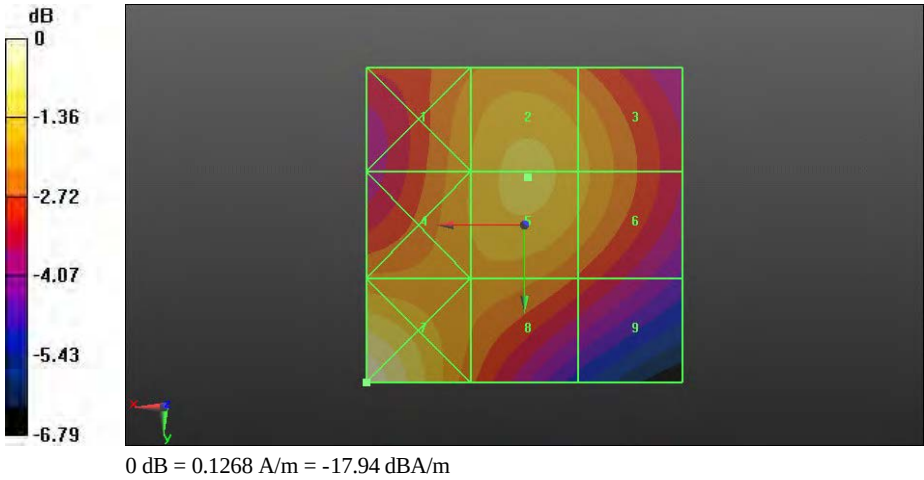
Grid 1 M4 0.103 A/m	Grid 2 M4 0.110 A/m	Grid 3 M4 0.105 A/m
Grid 4 M4 0.104 A/m	Grid 5 M4 0.110 A/m	Grid 6 M4 0.105 A/m
Grid 7 M4 0.127 A/m	Grid 8 M4 0.101 A/m	Grid 9 M4 0.092 A/m

Cursor:

Total = 0.1268 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band IV-1312CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1260 A/m; Power Drift = -0.01 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1113 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

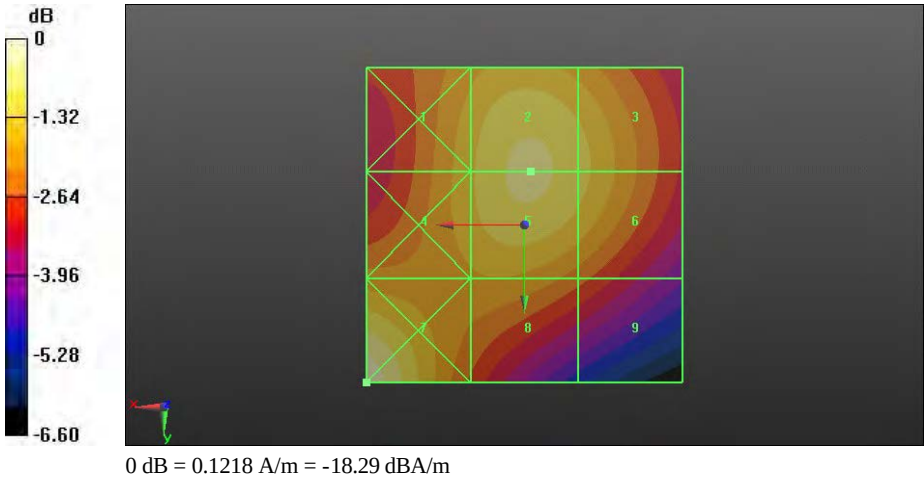
Grid 1 M4 0.104 A/m	Grid 2 M4 0.111 A/m	Grid 3 M4 0.107 A/m
Grid 4 M4 0.104 A/m	Grid 5 M4 0.111 A/m	Grid 6 M4 0.107 A/m
Grid 7 M4 0.122 A/m	Grid 8 M4 0.099 A/m	Grid 9 M4 0.092 A/m

Cursor:

Total = 0.1218 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band IV-1312CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1250 A/m; Power Drift = 0.03 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1094 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

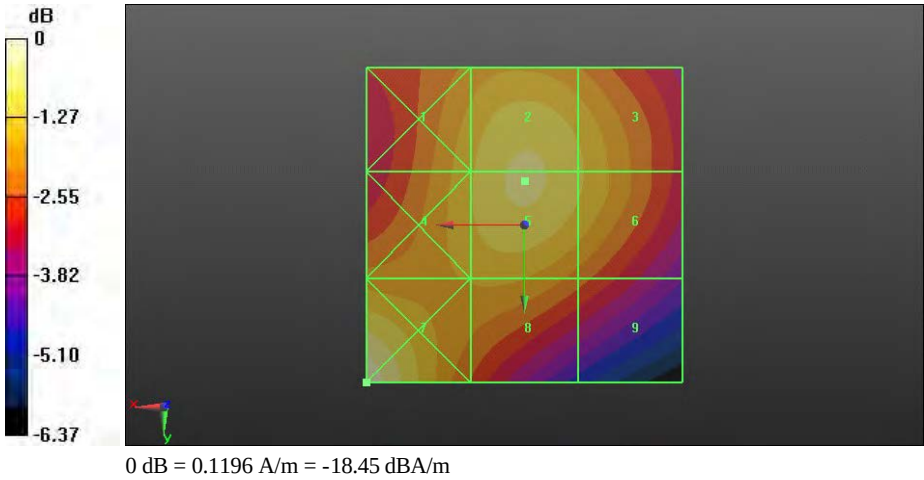
Grid 1 M4 0.103 A/m	Grid 2 M4 0.109 A/m	Grid 3 M4 0.104 A/m
Grid 4 M4 0.103 A/m	Grid 5 M4 0.109 A/m	Grid 6 M4 0.104 A/m
Grid 7 M4 0.120 A/m	Grid 8 M4 0.099 A/m	Grid 9 M4 0.091 A/m

Cursor:

Total = 0.1196 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band V-4233CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 87.77 V/m; Power Drift = -0.05 dB

PMF = 1.040 is applied.

E-field emissions = 70.47 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

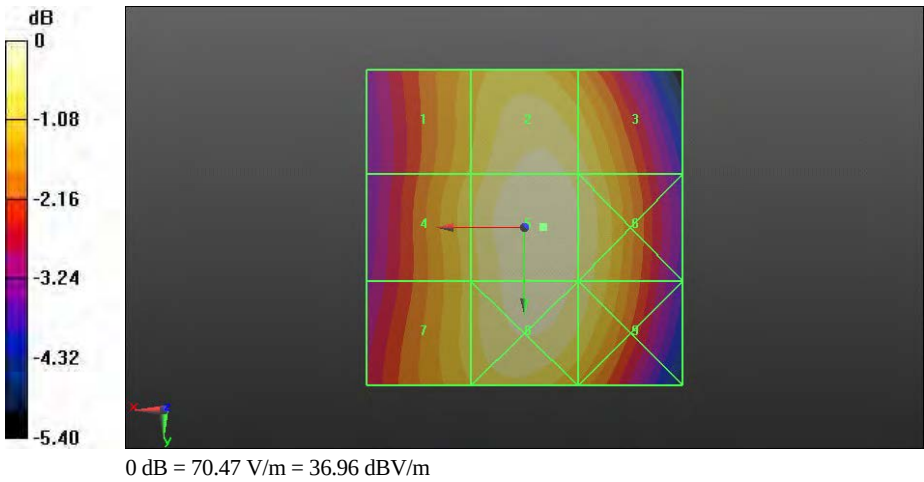
Grid 1 M4	Grid 2 M4	Grid 3 M4
62.85 V/m	68.82 V/m	66.36 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
64.34 V/m	70.47 V/m	68.00 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
63.69 V/m	69.41 V/m	67.02 V/m

Cursor:

Total = 70.47 V/m

E Category: M4

Location: -3, 0, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band V-4182CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 84.35 V/m; Power Drift = -0.02 dB

PMF = 1.040 is applied.

E-field emissions = 67.39 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

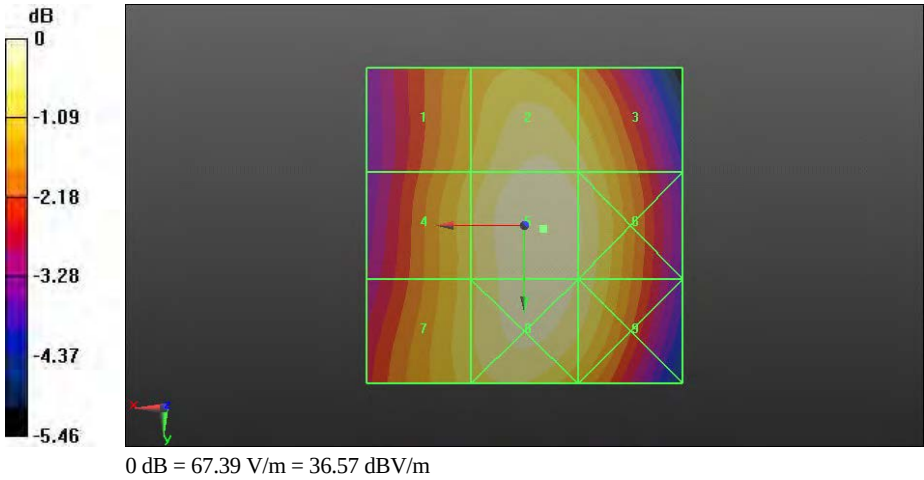
Grid 1 M4	Grid 2 M4	Grid 3 M4
59.81 V/m	65.46 V/m	63.28 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
61.58 V/m	67.39 V/m	65.12 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
61.56 V/m	66.68 V/m	64.42 V/m

Cursor:

Total = 67.39 V/m

E Category: M4

Location: -3, 0.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band V-4132CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 84.01 V/m; Power Drift = -0.02 dB

PMF = 1.040 is applied.

E-field emissions = 66.95 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

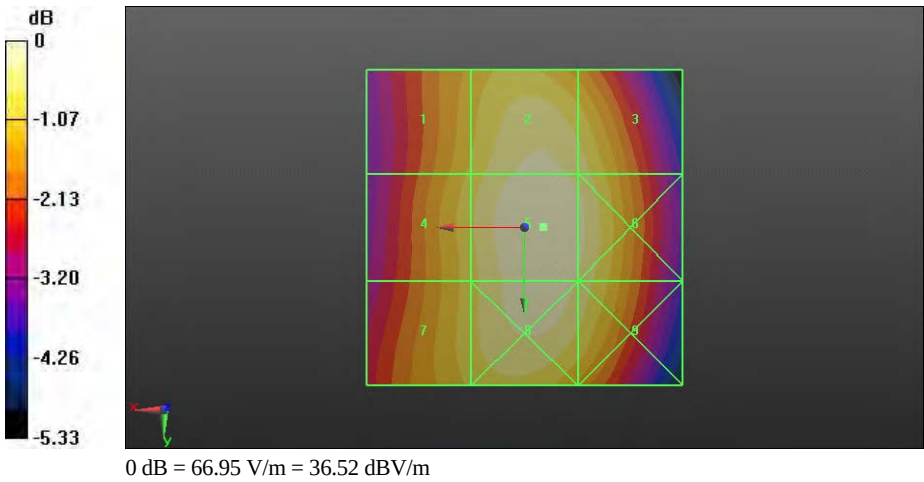
Grid 1 M4	Grid 2 M4	Grid 3 M4
59.83 V/m	65.27 V/m	63.38 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
61.29 V/m	66.95 V/m	65.10 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
60.84 V/m	66.26 V/m	63.84 V/m

Cursor:

Total = 66.95 V/m

E Category: M4

Location: -3, 0, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U8686-UMTS Band V-4233CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 86.92 V/m; Power Drift = 0.06 dB

PMF = 1.040 is applied.

E-field emissions = 70.51 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

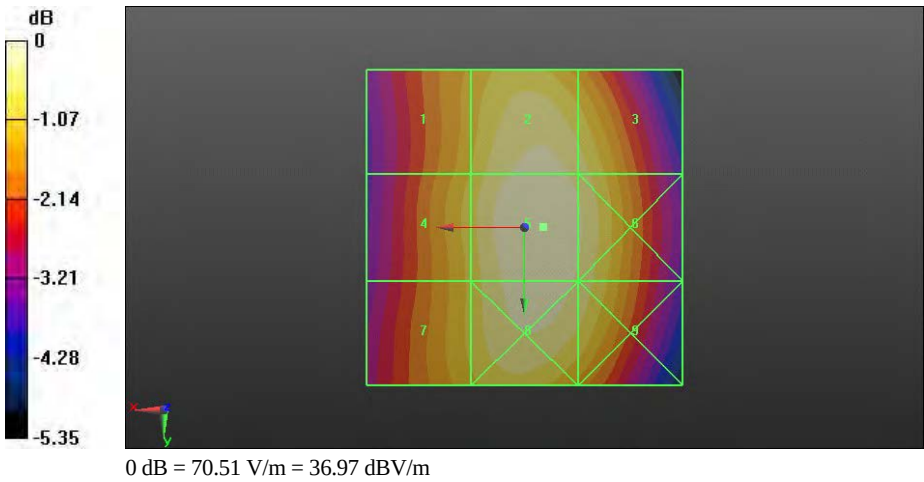
Grid 1 M4	Grid 2 M4	Grid 3 M4
62.55 V/m	68.95 V/m	66.65 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
63.98 V/m	70.51 V/m	68.23 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
63.19 V/m	69.45 V/m	67.18 V/m

Cursor:

Total = 70.51 V/m

E Category: M4

Location: -3, 0, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band V-4233CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06800 A/m; Power Drift = -0.01 dB

PMF = 1.020 is applied.

H-field emissions = 0.09624 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

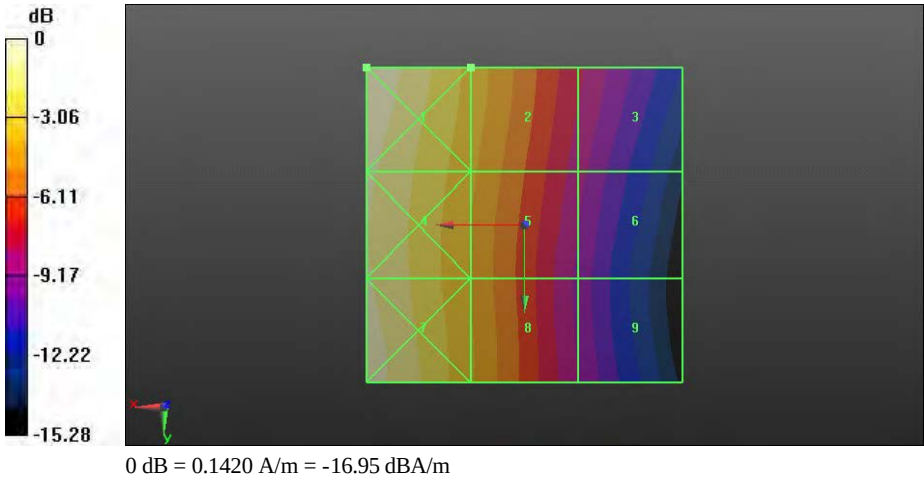
Grid 1 M4 0.142 A/m	Grid 2 M4 0.096 A/m	Grid 3 M4 0.057 A/m
Grid 4 M4 0.130 A/m	Grid 5 M4 0.091 A/m	Grid 6 M4 0.052 A/m
Grid 7 M4 0.136 A/m	Grid 8 M4 0.091 A/m	Grid 9 M4 0.050 A/m

Cursor:

Total = 0.1420 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band V-4182CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06600 A/m; Power Drift = -0.04 dB

PMF = 1.020 is applied.

H-field emissions = 0.09472 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

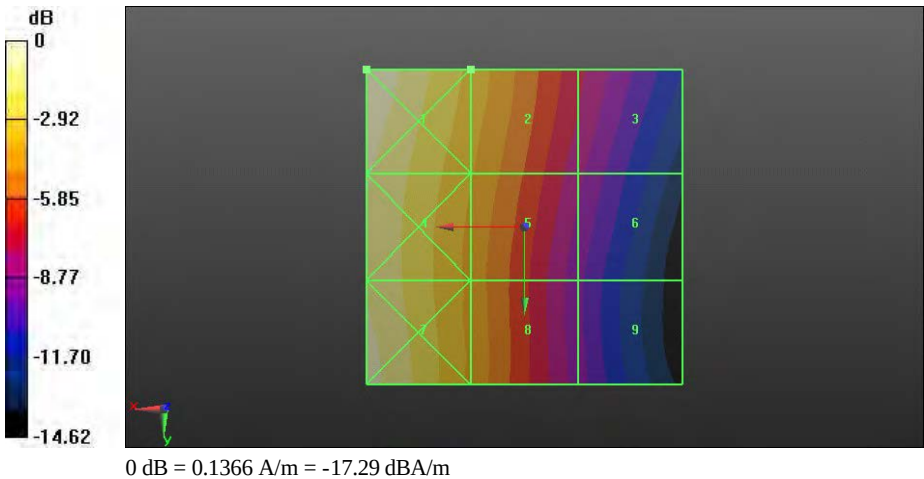
Grid 1 M4 0.137 A/m	Grid 2 M4 0.095 A/m	Grid 3 M4 0.058 A/m
Grid 4 M4 0.124 A/m	Grid 5 M4 0.088 A/m	Grid 6 M4 0.052 A/m
Grid 7 M4 0.128 A/m	Grid 8 M4 0.085 A/m	Grid 9 M4 0.047 A/m

Cursor:

Total = 0.1366 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band V-4132CH

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06500 A/m; Power Drift = -0.06 dB

PMF = 1.020 is applied.

H-field emissions = 0.09006 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

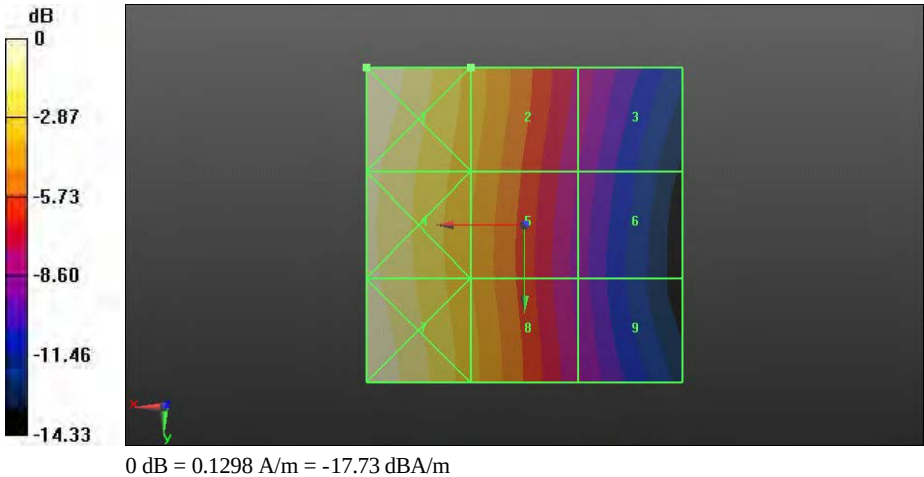
Grid 1 M4 0.132 A/m	Grid 2 M4 0.090 A/m	Grid 3 M4 0.053 A/m
Grid 4 M4 0.121 A/m	Grid 5 M4 0.086 A/m	Grid 6 M4 0.048 A/m
Grid 7 M4 0.130 A/m	Grid 8 M4 0.087 A/m	Grid 9 M4 0.049 A/m

Cursor:

Total = 0.1324 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U8686-UMTS Band V-4233CH with battery 2#

DUT: U8686; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06800 A/m; Power Drift = 0.04 dB

PMF = 1.020 is applied.

H-field emissions = 0.09535 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

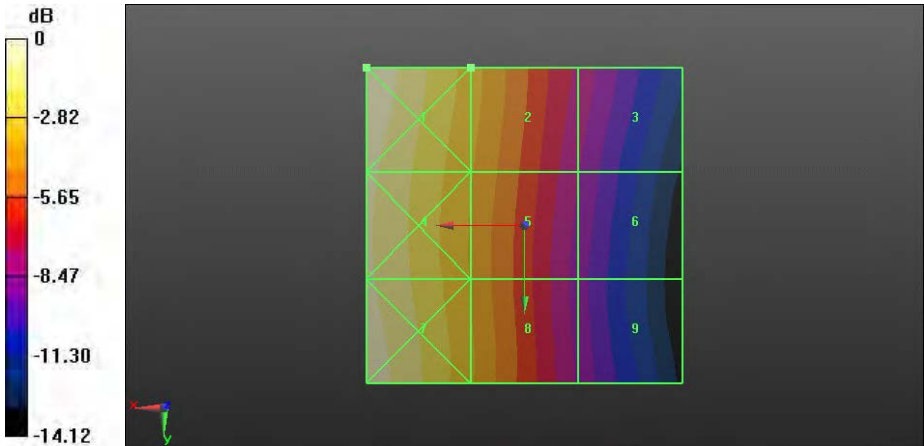
Grid 1 M4 0.139 A/m	Grid 2 M4 0.095 A/m	Grid 3 M4 0.057 A/m
Grid 4 M4 0.129 A/m	Grid 5 M4 0.091 A/m	Grid 6 M4 0.053 A/m
Grid 7 M4 0.134 A/m	Grid 8 M4 0.092 A/m	Grid 9 M4 0.052 A/m

Cursor:

Total = 0.1393 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1393 A/m = -17.12 dBA/m